



Supporting Information

2 One-Step Laser Patterned Highly Uniform Reduced	Ctrannen	Keaucea Gra	v Onitorm Reduced	HISHIA	aser Patterned	Laser	One-Steb	2
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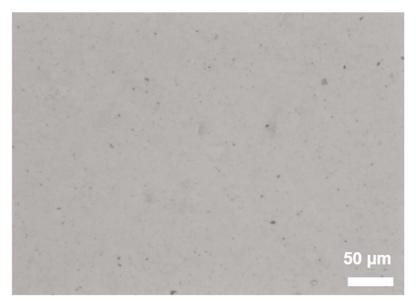
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- 6 Rowoon Park^{1,†}, Hyesu Kim^{1,†}, Saifullah Lone^{1,†}, Sangheon Jeon¹, Young Woo Kwon²,
- 7 Bosung Shin^{1,*} and Suck Won Hong^{1,*}
- 8 ¹ Department of Cogno-Mechatronics Engineering, Department of Optics and Mechatronics
- 9 Engineering, College of Nanoscience and Nanotechnology, Pusan National University,
- 10 Busan 46241, Republic of Korea.
- ² Department of Nano-Fusion Technology, College of Nanoscience and Nanotechnology,
- 12 Pusan National University, Busan 46241, Republic of Korea.
- * Correspondence: bosung@pusan.ac.kr (B.S.); swhong@pusan.ac.kr (S.W.H.)
- † These authors contributed equally to this work.

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Figure S1. OM image of highly uniform GO thin film (~40 nm) on APTES-treated PP substrate produced by FESA process.

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Parameter	Value		
Source	Nd:YVO4 UV pulsed laser		
Wavelength (nm)	355		
Average power (W)	0.8		
Pulse length (ns)	20		
Repetition rate (灺)	30		
Beam diameter (mm)	1.5		
Beam divergence (mrad)	< 0.5		
Beam Mode (m²)	< 1.25 TEM ₀₀		

Figure S2. Specification of laser system.

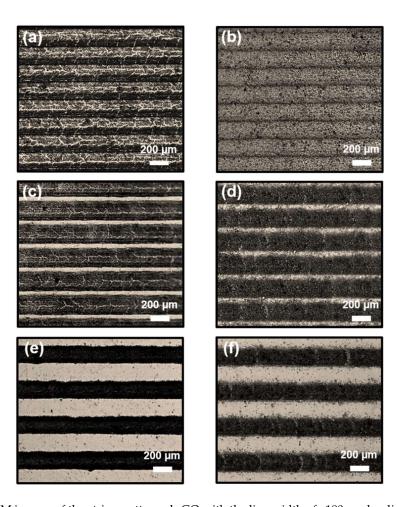


Figure S3. OM images of the stripe-patterned rGO with the line width of ~180 μ m by direct (left side) and indirect laser exposure (right side) under the condition of laser power 0.8 W and laser speed 100 mm/s; (a), (b):patterns of overlapping lines, (c), (d):line intervals of ~50 μ m and (e), (f):line intervals of ~200 μ m.

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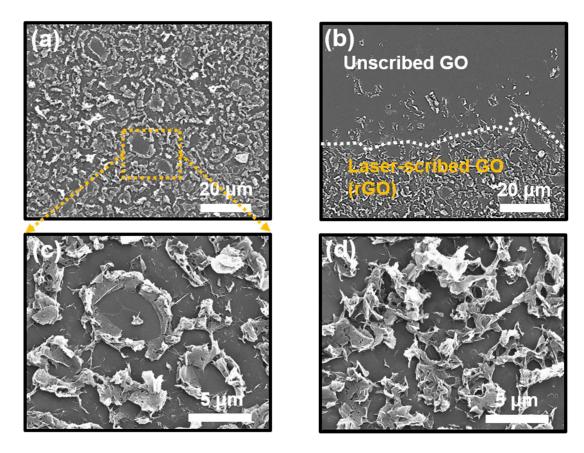


Figure S4. SEM images revealing the surface morphology of rGO film by indirect laser exposure through the PP barrier under the condition of laser power 0.8 W and laser speed 100 mm/s. (a) GO surface inside the indirectly laser-exposed region. (b) The boundary between laser exposed rGO region and unscribed region in GO thin film marked by the white dotted line. (c) and (d) highly magnified SEM images of rGO surface with surface craters and swollen structures formed by PP barrier at laser exposure.

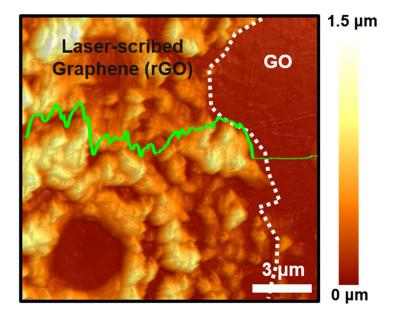
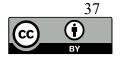


Figure S5. Representative AFM image of the noticeable interface differences between the laser-scribed GO region and unscribed GO region; Green line shows relative height profile (up to ~1.5 μ m) to the left and right area, bounding the white dotted line.

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